

### General Description

The WSD40120DN is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD40120DN meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

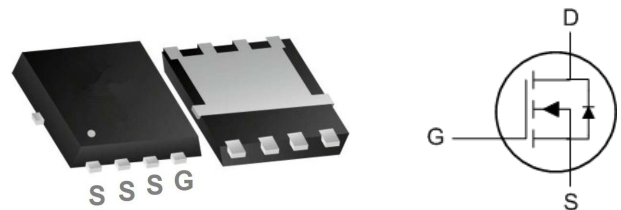
### Product Summary

BVDSS	RDSON	ID
40V	1.85mΩ	120A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

### DFN5X6-8 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,7}$	120	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,7}$	100	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	400	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	240	mJ
$I_{AS}$	Avalanche Current	31	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	104	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	1.2	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.043	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	1.85	2.4	mΩ
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	---	2.5	3.3	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.5	1.8	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-6.94	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	2	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	10	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	---	55	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.1	2	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =40A	---	76	91	nC
Q <sub>gs</sub>	Gate-Source Charge		---	12	14.4	
Q <sub>gd</sub>	Gate-Drain Charge		---	15.5	18.6	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GEN</sub> =10V, R <sub>G</sub> =1Ω, I <sub>D</sub> =1A, RL=15Ω.	---	20	24	ns
T <sub>r</sub>	Rise Time		---	10	12	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	58	69	
T <sub>f</sub>	Fall Time		---	34	40	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	3450	4350	5220	pF
C <sub>oss</sub>	Output Capacitance		580	690	800	
C <sub>rss</sub>	Reverse Transfer Capacitance		300	370	450	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.5mH, I <sub>AS</sub> =31A	198	---	---	mJ

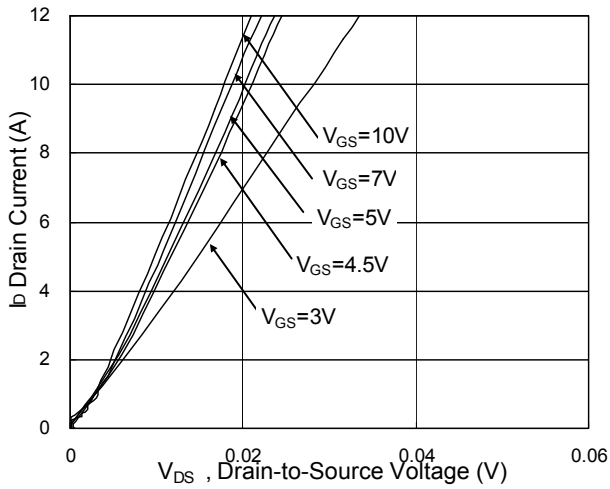
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	100	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	400	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A, T <sub>J</sub> =25°C	---	---	1.1	V

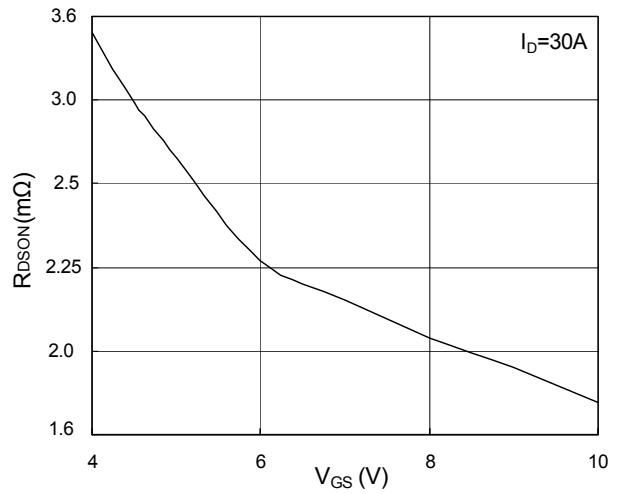
Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.5mH, I<sub>AS</sub>=31A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.
- Package limitation current is 100A.

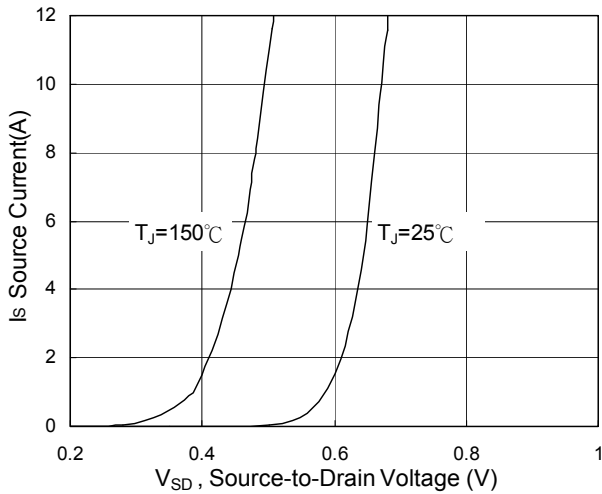
**Typical Characteristics**



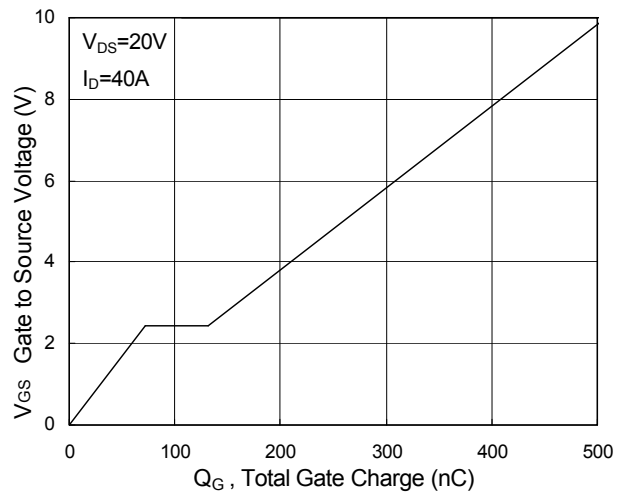
**Fig.1 Typical Output Characteristics**



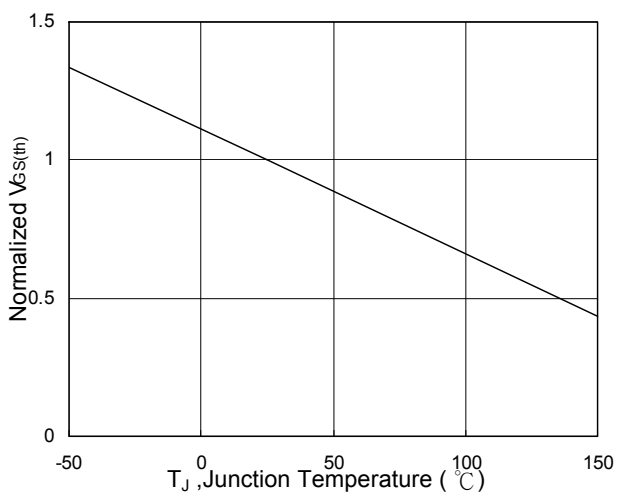
**Fig.2 On-Resistance v.s Gate-Source**



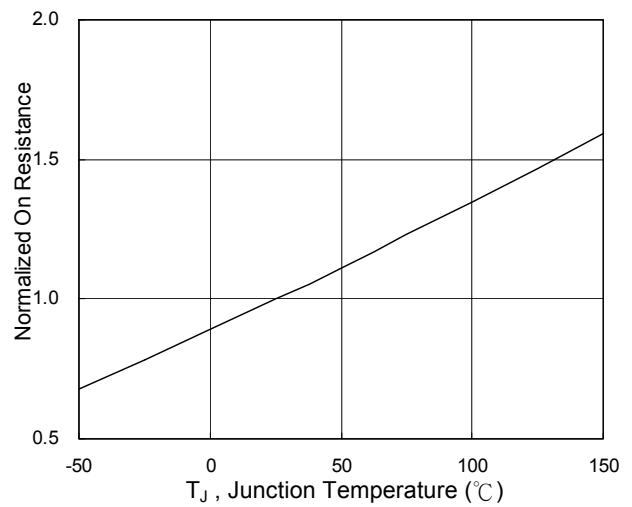
**Fig.3 Forward Characteristics of Reverse**



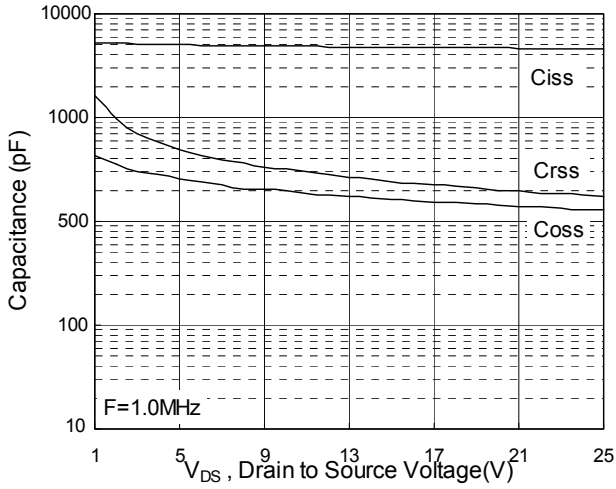
**Fig.4 Gate-Charge Characteristics**



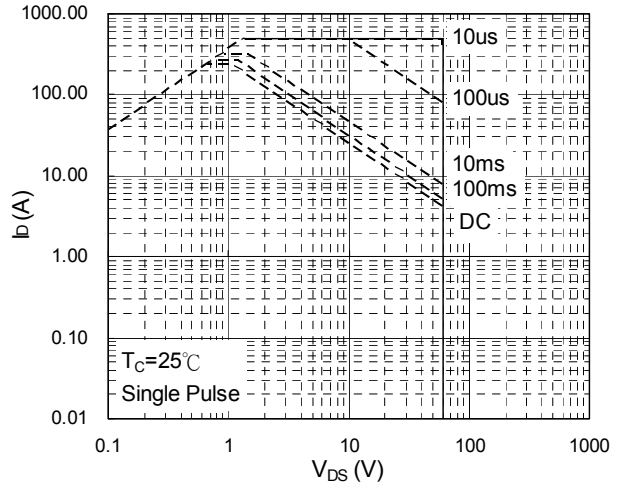
**Fig.5 Normalized V<sub>GS(th)</sub> v.s T<sub>J</sub>**



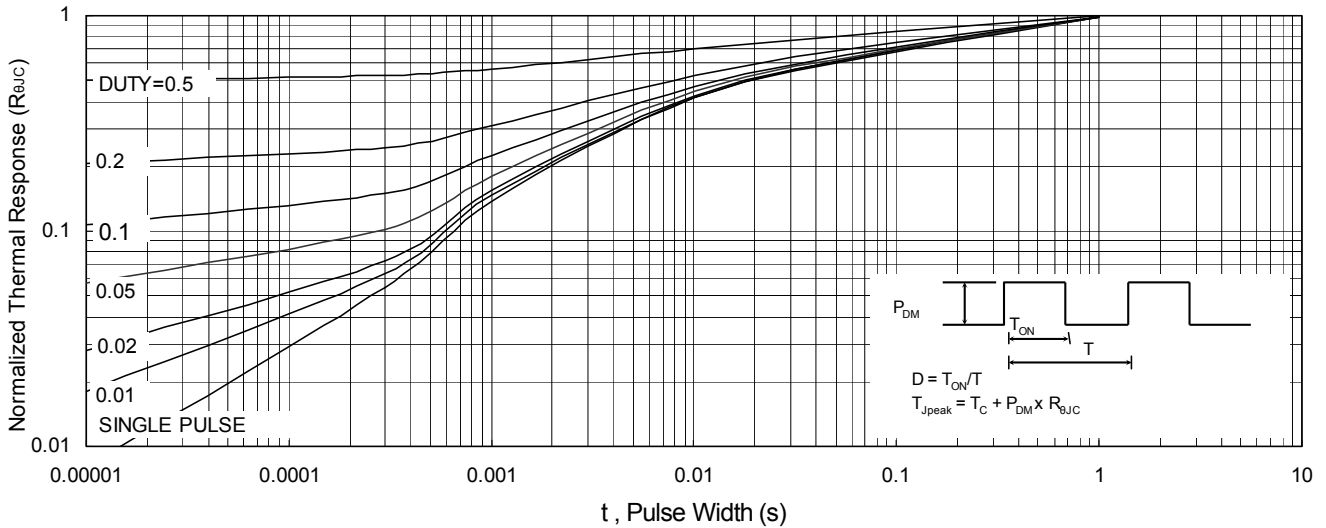
**Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>**



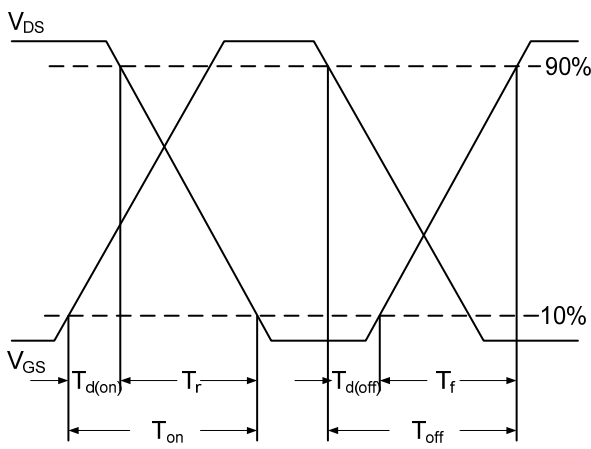
**Fig.7 Capacitance**



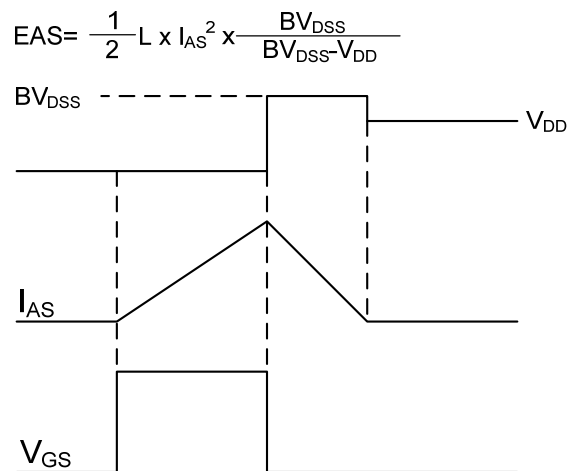
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Waveform**